

# N-Channel 200-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
200	0.480 at V <sub>GS</sub> = 10 V	1.50		
	0.510 at V <sub>GS</sub> = 6.0 V	1.45		

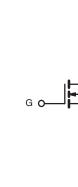
### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- · PWM Optimized for fast Switching
- Compliant to RoHS Directive 2002/95/EC

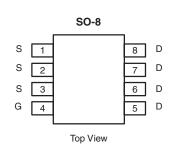


## **APPLICATIONS**

· Primary Side Switch



N-Channel MOSFET



Ordering Information: Si4462DY-T1-E3 (Lead (Pb)-free)

Si4462DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

<b>ABSOLUTE MAXIMUM RATINGS</b>	T <sub>A</sub> = 25 °C, unle	ss otherwise r	noted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V <sub>DS</sub>	200		V
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Ocation	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	1.50	1.15	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		1.20	0.92	
Pulsed Drain Current		I <sub>DM</sub>	5		Α
Single Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	1.5		
Single Avalanche Energy	L = U.T IIIII	E <sub>AS</sub>	0.11		mJ
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	2.1	1.1	Α
Manipus Barra Distriction	T <sub>A</sub> = 25 °C	P_	2.5	1.3	W
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C	- P <sub>D</sub>	1.6	0.85	VV
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manifestor Localitan to Applicant	t ≤ 10 s	- R <sub>thJA</sub>	40	50		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		70	85	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	20	24		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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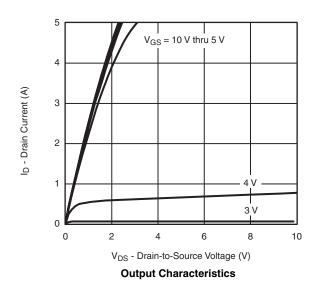
<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions Min. Ty		Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.0		4	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zava Cata Valtaga Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 200 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current		$V_{DS}$ = 200 V, $V_{GS}$ = 0 V, $T_{J}$ = 55 °C			5	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	5			Α	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.5 A		0.39	0.480	0	
Drain-Source On-State Resistance <sup>a</sup>		$V_{GS} = 6.0 \text{ V}, I_D = 1.45 \text{ A}$		0.420	0.510	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 1.5 A		5		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 2.1 A, V <sub>GS</sub> = 0 V		0.8	1.2	V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_g$			6	9		
Gate-Source Charge	Q <sub>gs</sub>	<del></del>		0.9		nC	
Gate-Drain Charge	$Q_{gd}$			1.9			
Gate Resistance	$R_g$			3.7		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			10	15		
Rise Time	t <sub>r</sub>	$ \begin{array}{c c} t_r & V_{DD} = 100 \text{ V}, \text{ R}_L = 100 \Omega \\ \hline t_{d(off)} & I_D \cong 1.0 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 6 \Omega \\ \end{array} $		12	20	ns	
Turn-Off Delay Time	t <sub>d(off)</sub>			10	15		
Fall Time	t <sub>f</sub>			15	25		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	$I_F = 2.1 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}$		55	90		

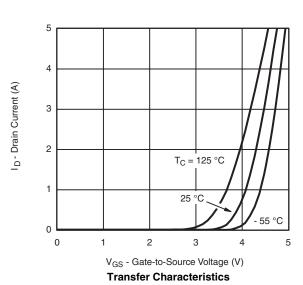
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

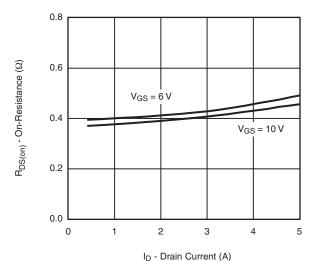




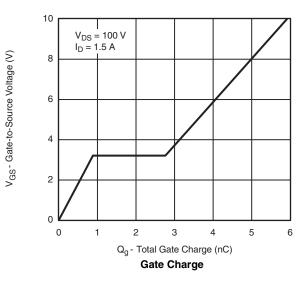


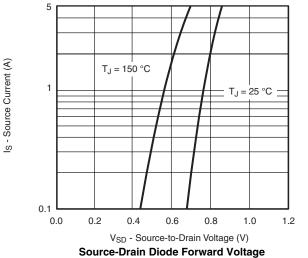


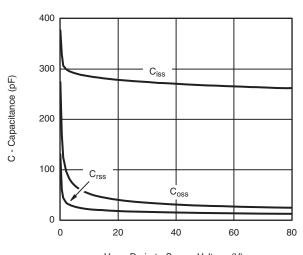
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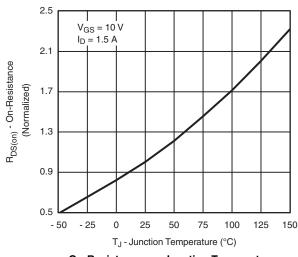
**On-Resistance vs. Drain Current** 



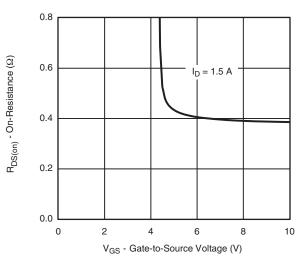




V<sub>DS</sub> - Drain-to-Source Voltage (V) **Capacitance** 



On-Resistance vs. Junction Temperature

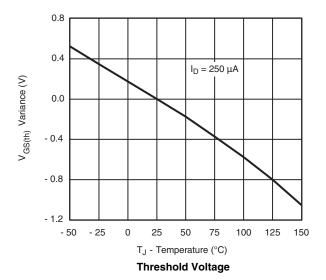


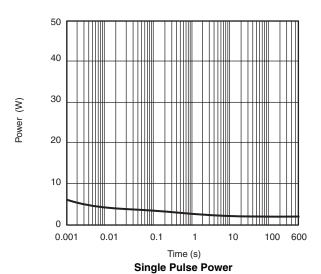
On-Resistance vs. Gate-to-Source Voltage

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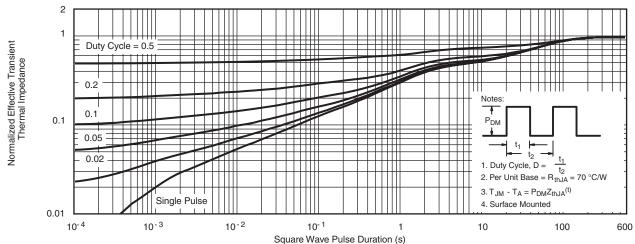
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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





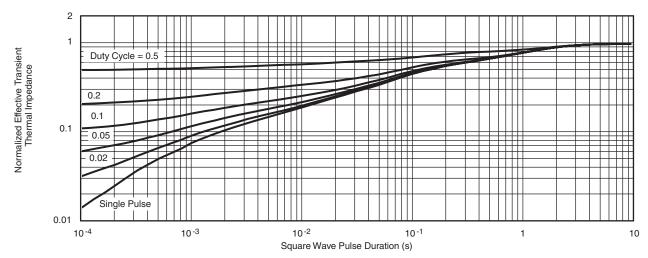




Normalized Thermal Transient Impedance, Junction-to-Ambient



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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